NTTS2P03R2

Power MOSFET
-2.48 Amps, -30 Volts

P–Channel Enhancement Mode
Single Micro8™ Package

Features
- Ultra Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- Miniature Micro8 Surface Mount Package
- Diode Exhibits High Speed, Soft Recovery
- Micro8 Mounting Information Provided
- Pb−Free Package is Available

Applications
- Power Management in Portable and Battery−Powered Products, i.e.: Cellular and Cordless Telephones and PCMCIA Cards

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	−30	V
Gate−to−Source Voltage – Continuous	V_{GS}	±20	V
Thermal Resistance, Junction−to−Ambient (Note 1)	$R_{\theta JA}$	160	°C/W
Total Power Dissipation @ T_A = 25°C	P_D	0.78	W
Continuous Drain Current @ T_A = 25°C	I_D	−2.48	A
Continuous Drain Current @ T_A = 70°C	I_D	−1.98	A
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	70	°C/W
Total Power Dissipation @ T_A = 25°C	P_D	1.78	W
Continuous Drain Current @ T_A = 25°C	I_D	−3.75	A
Continuous Drain Current @ T_A = 70°C	I_D	−3.0	A
Thermal Resistance, Junction−to−Ambient (Note 3)	$R_{\theta JA}$	210	°C/W
Total Power Dissipation @ T_A = 25°C	P_D	0.60	W
Continuous Drain Current @ T_A = 25°C	I_D	−2.10	A
Continuous Drain Current @ T_A = 70°C	I_D	−1.67	A
Pulsed Drain Current (Note 5)	I_{DM}	−17	A
Thermal Resistance , Junction−to−Ambient (Note 4)	$R_{\theta JA}$	100	°C/W
Total Power Dissipation @ T_A = 25°C	P_D	1.25	W
Continuous Drain Current @ T_A = 25°C	I_D	−3.02	A
Continuous Drain Current @ T_A = 70°C	I_D	−2.42	A
Pulsed Drain Current (Note 5)	I_{DM}	−24	A
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.
1. Minimum FR−4 or G−10 PCB, Time ≤ 10 Seconds.
2. Mounted onto a 2″ square FR−4 Board (1″ sq. 2 oz Cu 0.06″ thick single sided), Time ≤ 10 Seconds.
3. Minimum FR−4 or G−10 PCB, Steady State.
4. Mounted onto a 2″ square FR−4 Board (1″ sq. 2 oz Cu 0.06″ thick single sided), Steady State.
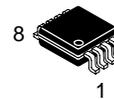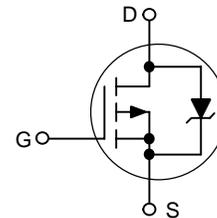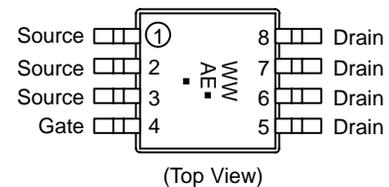5. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

ON Semiconductor®

http://onsemi.com

−2.48 AMPERES
−30 VOLTS
85 mΩ @ V_{GS} = −10 V

Single P−Channel

Micro8
CASE 846A
STYLE 1

MARKING DIAGRAM & PIN ASSIGNMENT

Source	1	8 Drain
Source	2	7 Drain
Source	3	6 Drain
Gate	4	5 Drain

WW AE (Top View)

WW	=	Work Week
AE	=	Device Code
▪	=	Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTTS2P03R2	Micro8	4000/Tape & Reel
NTTS2P03R2G	Micro8 (Pb−Free)	4000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted) (continued)

Rating	Symbol	Value	Unit
Single Pulse Drain–to–Source Avalanche Energy – Starting T_J = 25°C (V_{DD} = –30 Vdc, V_{GS} = –10 Vdc, Peak I_L = –3.0 Apk, L = 65 mH, R_G = 25 Ω)	E_{AS}	292.5	mJ
Maximum Lead Temperature for Soldering Purposes for 10 seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted) (Note 6)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain–to–Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = –250 μAdc) Temperature Coefficient (Positive)	$V_{(BR)DSS}$	–30 –	– –30	– –	Vdc mV/°C
Zero Gate Voltage Drain Current (V_{GS} = 0 Vdc, V_{DS} = –30 Vdc, T_J = 25°C) (V_{GS} = 0 Vdc, V_{DS} = –30 Vdc, T_J = 125°C)	I_{DSS}	– –	– –	–1.0 –25	μAdc
Gate–Body Leakage Current (V_{GS} = –20 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	–	–	–100	nAdc
Gate–Body Leakage Current (V_{GS} = +20 Vdc, V_{DS} = 0 Vdc)	I_{GSS}	–	–	100	nAdc
ON CHARACTERISTICS					
Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = –250 μAdc) Temperature Coefficient (Negative)	$V_{GS(th)}$	–1.0 –	–1.7 3.6	–3.0 –	Vdc
Static Drain–to–Source On–State Resistance (V_{GS} = –10 Vdc, I_D = –2.48 Adc) (V_{GS} = –4.5 Vdc, I_D = –1.24 Adc)	$R_{DS(on)}$	– –	0.063 0.100	0.085 0.135	Ω
Forward Transconductance (V_{DS} = –15 Vdc, I_D = –1.24 Adc)	g_{FS}	–	3.1	–	Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	C_{iss}	–	500	–	pF
Output Capacitance	C_{oss}	–	160	–	
Reverse Transfer Capacitance	C_{rss}	–	65	–	

Dynamic characteristics condition: (V_{DS} = –24 Vdc, V_{GS} = 0 Vdc, f = 1.0 MHz)

SWITCHING CHARACTERISTICS (Notes 7 & 8)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Turn–On Delay Time	(V_{DD} = –24 Vdc, I_D = –2.48 Adc, V_{GS} = –10 Vdc, R_G = 6.0 Ω)	$t_{d(on)}$	–	10	–	ns
Rise Time		t_r	–	20	–	
Turn–Off Delay Time		$t_{d(off)}$	–	40	–	
Fall Time		t_f	–	35	–	
Turn–On Delay Time	(V_{DD} = –24 Vdc, I_D = –1.24 Adc, V_{GS} = –4.5 Vdc, R_G = 6.0 Ω)	$t_{d(on)}$	–	16	–	ns
Rise Time		t_r	–	40	–	
Turn–Off Delay Time		$t_{d(off)}$	–	30	–	
Fall Time		t_f	–	30	–	
Total Gate Charge	(V_{DS} = –24 Vdc, V_{GS} = –4.5 Vdc, I_D = –2.48 Adc)	Q_{tot}	–	15	22	nC
Gate–Source Charge		Q_{gs}	–	3.2	–	
Gate–Drain Charge		Q_{gd}	–	4.0	–	

BODY–DRAIN DIODE RATINGS (Note 7)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Diode Forward On–Voltage	(I_S = –2.48 Adc, V_{GS} = 0 Vdc) (I_S = –2.48 Adc, V_{GS} = 0 Vdc, T_J = 125°C)	V_{SD}	– –	–0.92 –0.72	–1.3 –	Vdc
Reverse Recovery Time	(I_S = –1.45 Adc, V_{GS} = 0 Vdc, dI_S/dt = 100 A/μs)	t_{rr}	–	38	–	ns
		t_a	–	20	–	
		t_b	–	18	–	
Reverse Recovery Stored Charge		Q_{RR}	–	0.04	–	μC

6. Handling precautions to protect against electrostatic discharge is mandatory.
7. Indicates Pulse Test: Pulse Width = 300 μsec max, Duty Cycle = 2%.
8. Switching characteristics are independent of operating junction temperature.
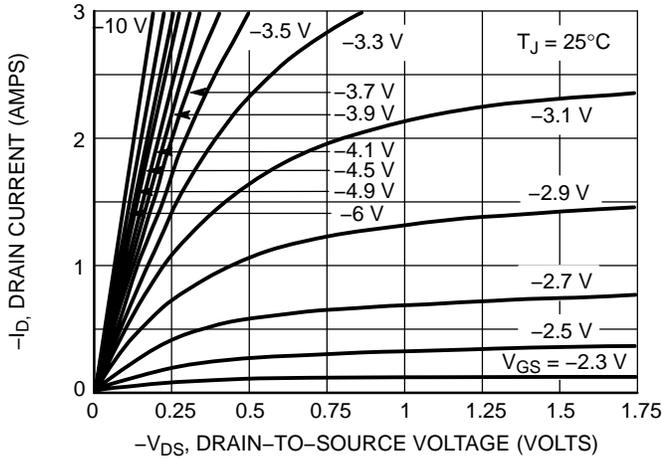
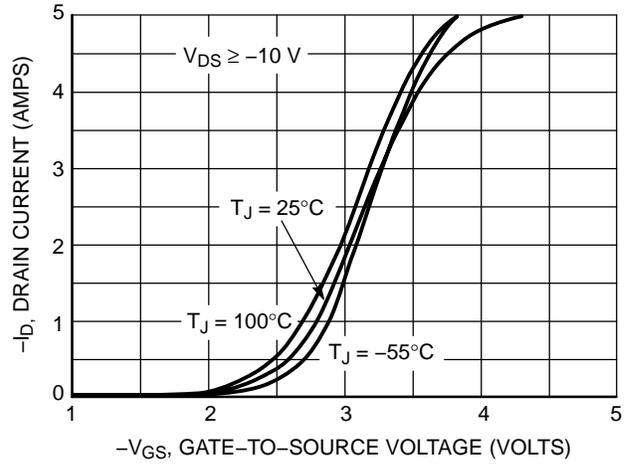# NTTS2P03R2

Figure 1. On–Region Characteristics
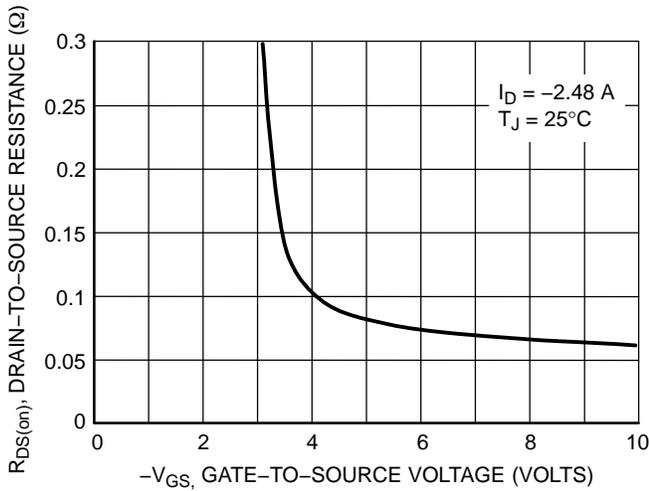

Figure 2. Transfer Characteristics

**Figure 3. On–Resistance versus
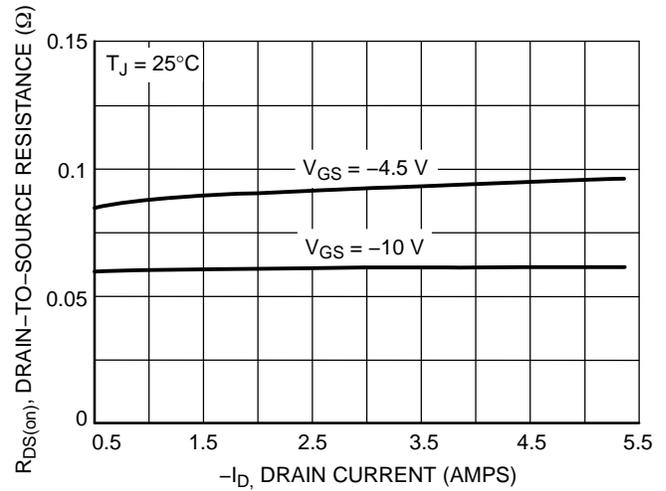Gate–to–Source Voltage**

**Figure 4. On–Resistance versus Drain Current
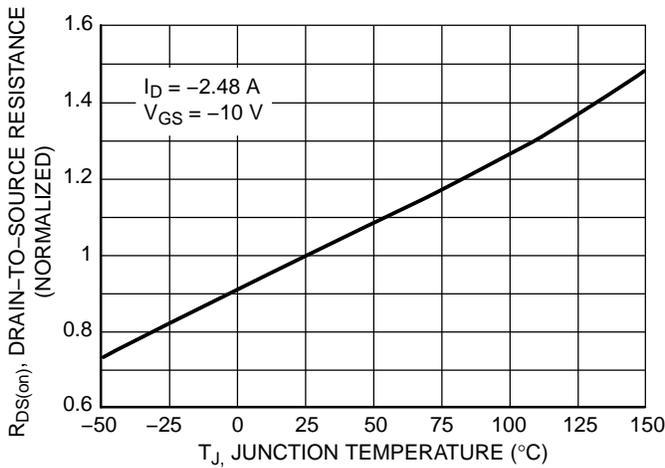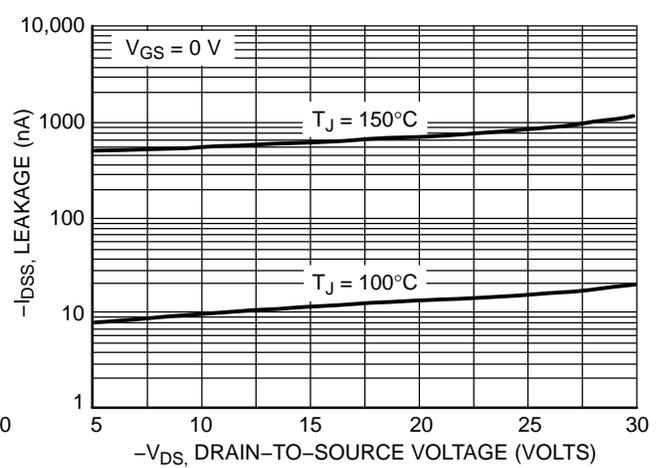and Gate Voltage**

**Figure 5. On–Resistance Variation with
Temperature**

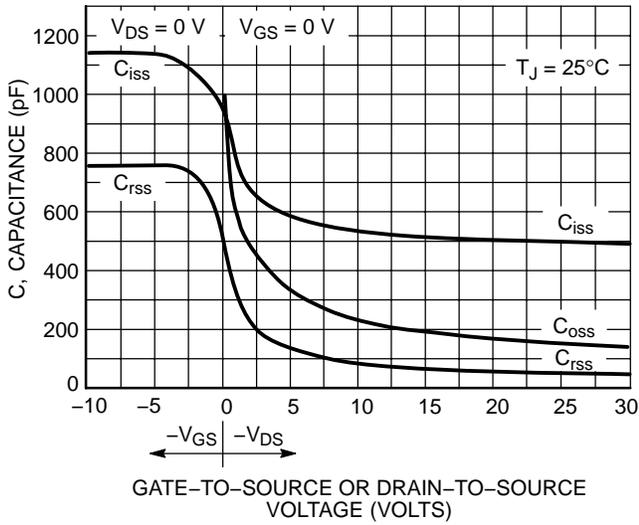
**Figure 6. Drain–to–Source Leakage Current
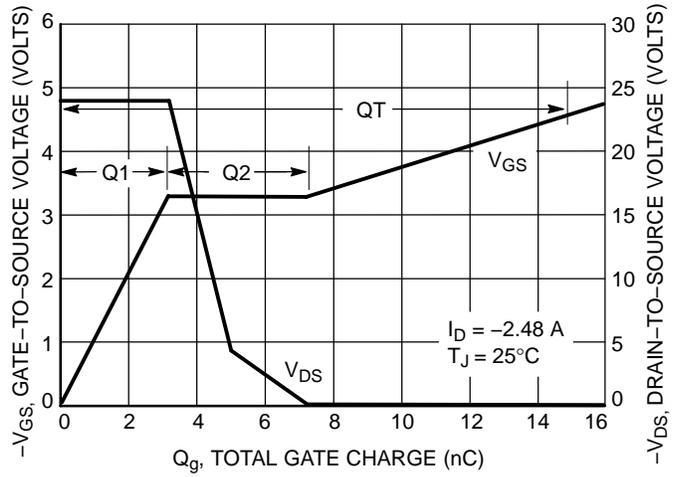versus Voltage**

Figure 7. Capacitance Variation

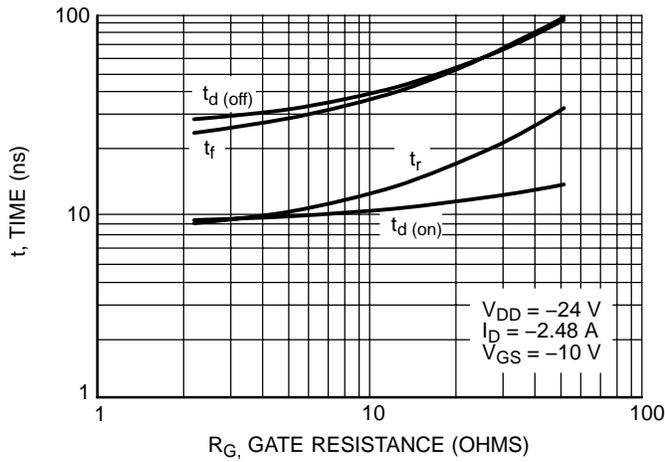**Figure 8. Gate–to–Source and
Drain–to–Source Voltage versus Total Charge**

**Figure 9. Resistive Switching Time Variation
versus Gate Resistance**
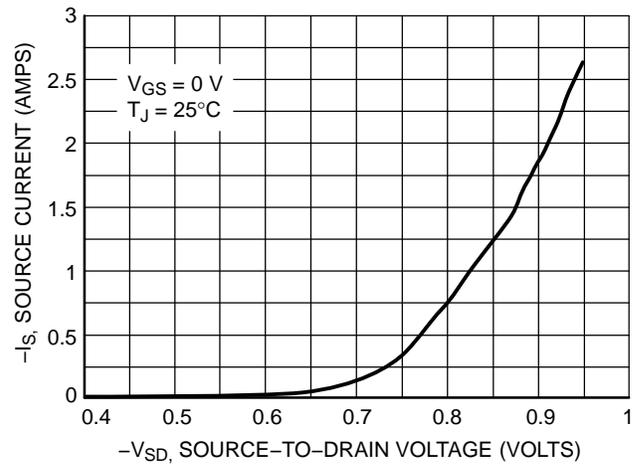
**Figure 10. Diode Forward Voltage
versus Current**
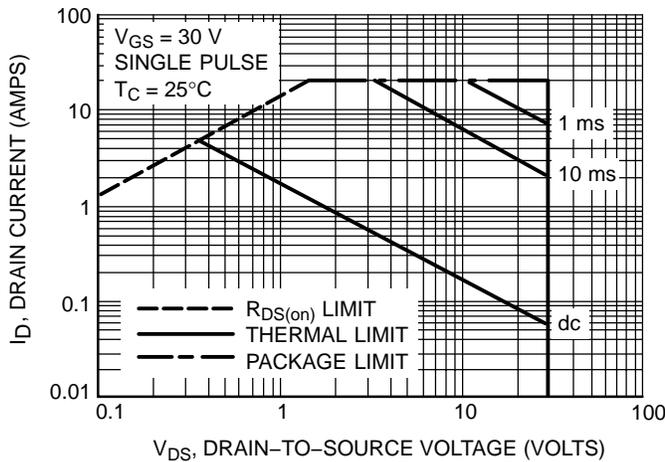
**Figure 11. Maximum Rated Forward Biased
Safe Operating Area**
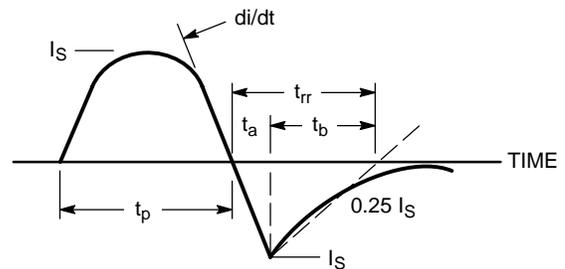
Figure 12. Diode Reverse Recovery Waveform

NTTS2P03R2

TYPICAL ELECTRICAL CHARACTERISTICS
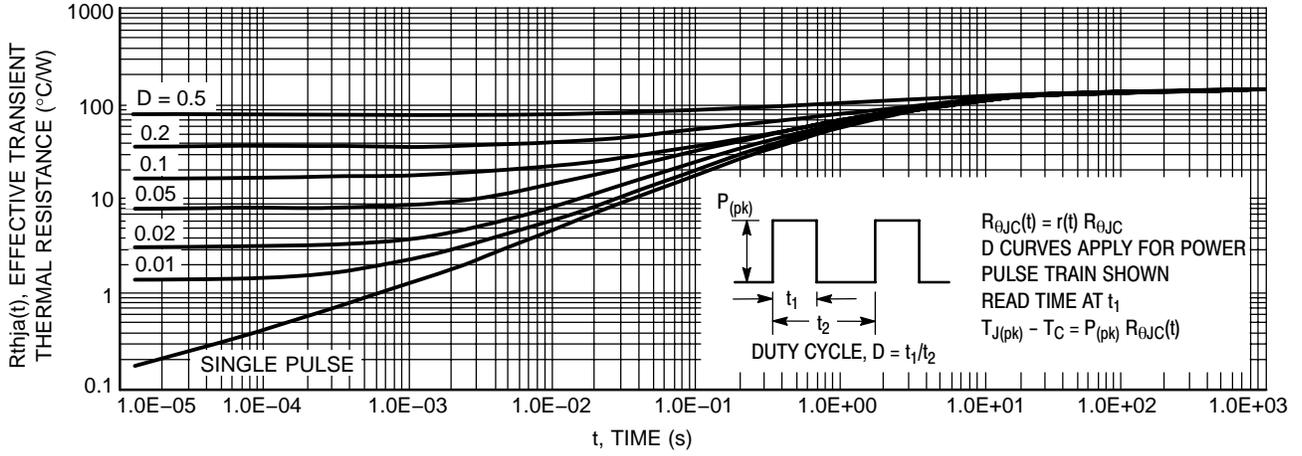
Figure 13. Thermal Response

NTTS2P03R2

PACKAGE DIMENSIONS

Micro8
CASE 846A–02
ISSUE F

PIN 1 ID

D 8 PL

$\oplus$ | 0.08 (0.003) Ⓜ | T | B Ⓢ | A Ⓢ

–T– **SEATING PLANE**
△ | 0.038 (0.0015)
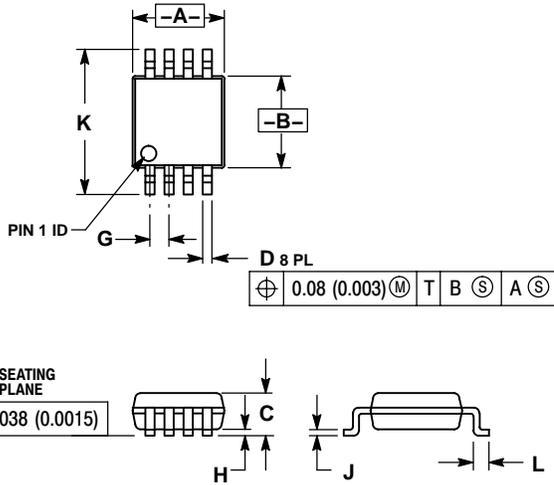
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. 846A–01 OBSOLETE, NEW STANDARD 846A–02.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.10	0.114	0.122
B	2.90	3.10	0.114	0.122
C	---	1.10	---	0.043
D	0.25	0.40	0.010	0.016
G	0.65 BSC		0.026 BSC	
H	0.05	0.15	0.002	0.006
J	0.13	0.23	0.005	0.009
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

SOLDERING FOOTPRINT*

8X $\frac{1.04}{0.041}$

$\frac{0.38}{0.015}$ 8X

$\frac{3.20}{0.126}$

$\frac{4.24}{0.167}$ $\frac{5.28}{0.208}$

6X $\frac{0.65}{0.0256}$

SCALE 8:1 $\left(\frac{mm}{inches}\right)$
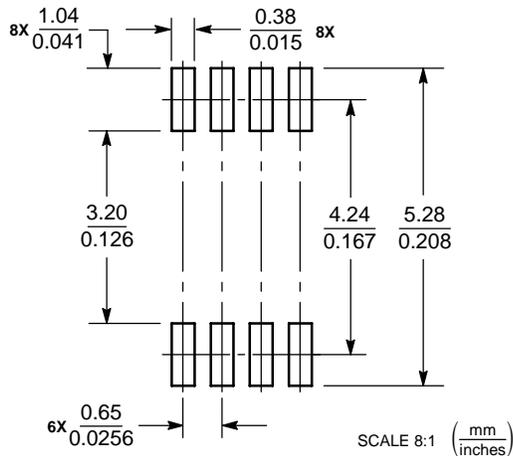
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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